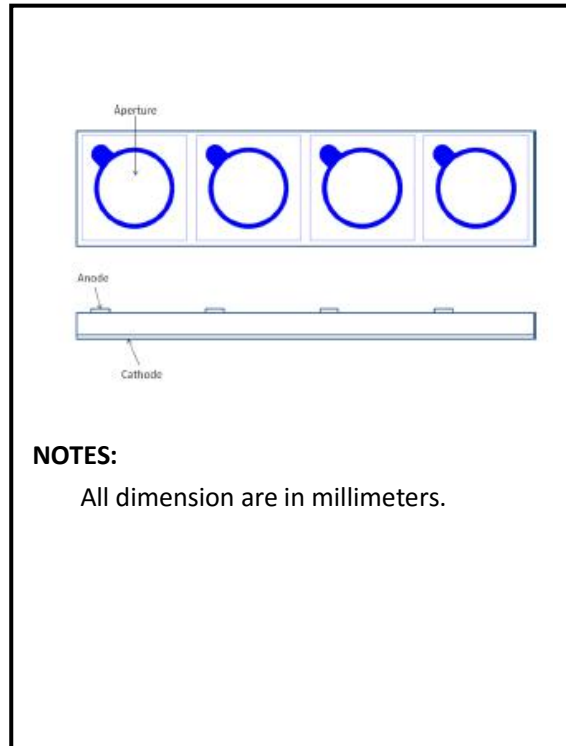
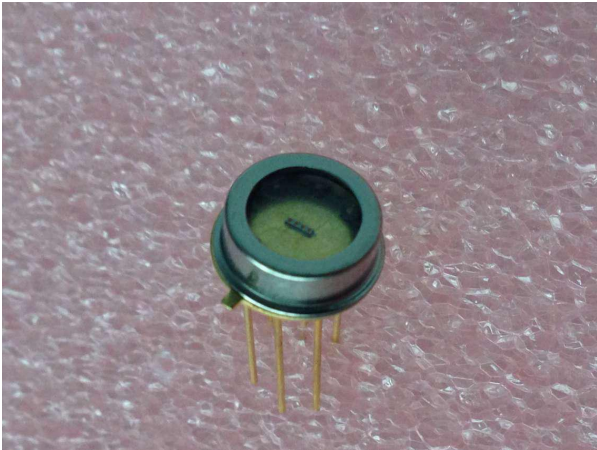


## InGaAs photodiode Array

### IGA0.25-4A



## Description

The IGA0.25-4A is high-output, high-speed InGaAs photo diode array , it's packaged on TO-39 metal CAN and permits wide angular response.

## Features

- \* High speed response from 800nm to 1700nm.
- \* Wide angular response
- \* High reliability in demanding environments
- \* Operating temperature is from -40 to +80°C
- \* Storage temperature is from -40 to +100°C
- \* soldering temperature is 260°C @Max.5 seconds at the position of 2mm from the PIN leg.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

OTRON ELE CTRONIC TECHNOLOGY CO.LTD

TEL:+86-21-54971821

FAX:+86-21-54971823

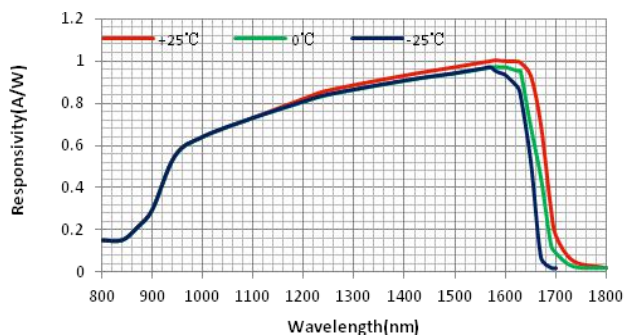
EMAL:frank.shuai@e-otron.com

<http://en.e-otron.com>



## Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	S	0.38*0.38*4				mm
Active area	A	Φ250				um
Forward current	I <sub>F</sub>	10				mA
Reverse current	I <sub>R</sub>	10				mA
Dark current	I <sub>D</sub>	V <sub>R</sub> =0V		0.1	1	nA
		V <sub>R</sub> =5V		1		
Rise time	t <sub>R</sub>	V <sub>R</sub> =5V;λ=850nm;R <sub>L</sub> =50Ω		0.8		ns
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =1uA		0.55	0.7	V
Reverse breakdown voltage	V <sub>(BR)R</sub>	I <sub>R</sub> =10μA Ev=0lx		30	42	V
Junction Capacitance	C <sub>J</sub>	V <sub>R</sub> =0V f=1MHz		1		nF
		V <sub>R</sub> =5V f=1MHz			4	pF
Photo sensitivity	S <sub>R</sub>	1310nm		0.95	0.97	A/W
		1550nm		0.98	1.10	
Spectral Application Range	λ <sub>range</sub>			1000	1680	nm
Spectral Response-Peak	λ <sub>p</sub>				1600	nm
Shunt resistance	R <sub>sh</sub>	V <sub>R</sub> =10mV		0.5		GΩ
Saturation power	L	V <sub>R</sub> =0V;λ=1.55μm		1	1	mW
		V <sub>R</sub> =2V;λ=1.55μm		2	8.2	
		V <sub>R</sub> =5V;λ=1.55μm		6	13.5	
Angular Resp 50% Resp Pt	θ <sub>1/2</sub>				±55	Degrees
Noise Equivalent Power	NEP	V <sub>R</sub> =5V λ=1550nm			5.16×10 <sup>-13</sup>	W/Hz <sup>1/2</sup>
Specific Detectivity	D*	V <sub>R</sub> =5V λ=1550nm			1.72×10 <sup>11</sup>	cm(Hz/W) <sup>1/2</sup>



Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

OTRON ELE CTRONIC TECHNOLOGY CO.LTD

TEL:+86-21-54971821  
FAX:+86-21-54971823

EMAL:frank.shuai@e-otron.com  
<http://en.e-otron.com>